

Abstract of the Disclosure:

A semiconductor device comprises a relatively lower threshold level MOSFET and relatively higher threshold level MOSFETs of n- and p-types. The higher threshold level MOSFETs have gate oxide films which is thicker than that of the lower threshold level MOSFET and, in addition, the gate oxide film of the higher threshold level MOSFET of n-type is thicker than that of the higher threshold level MOSFET of p-type. To fabricate the semiconductor device, implantation treatments of fluorine ions are carried out before the gate oxide treatment. Specifically, as for the higher threshold level MOSFETs of n- and p- types, implantation treatments of fluorine ions are independently carried out with unique implantation conditions.

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